

描述 / Descriptions

TO-252 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a TO-252 Plastic Package.

特征 / Features

高击穿电压，极好的放大线性，芯片采用 MBIT 技术。

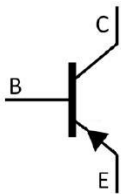
High breakdown voltage, adoption of MBIT process excellent h_{FE} linearity

用途 / Applications

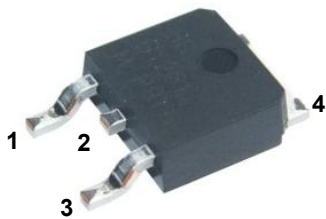
主要用于高压驱动。

High voltage driver applications.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : Base

PIN 2,4 : Collector

PIN 3 : Emitter

放大及印章代码 / h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	D	E
h_{FE} Range	60~120	100~200

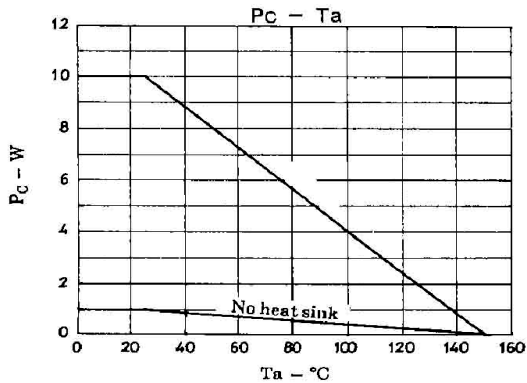
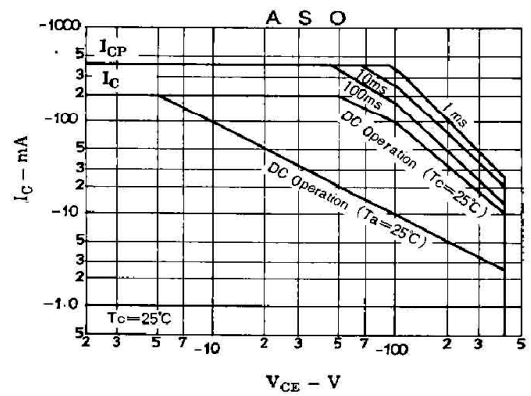
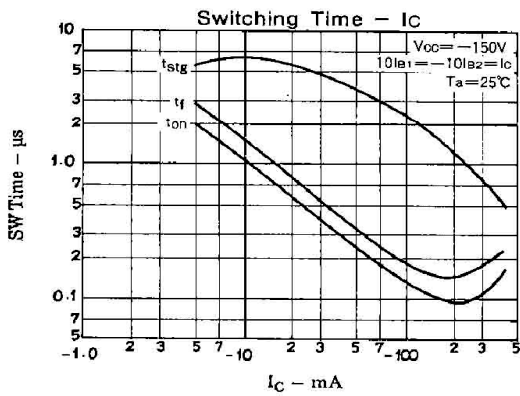
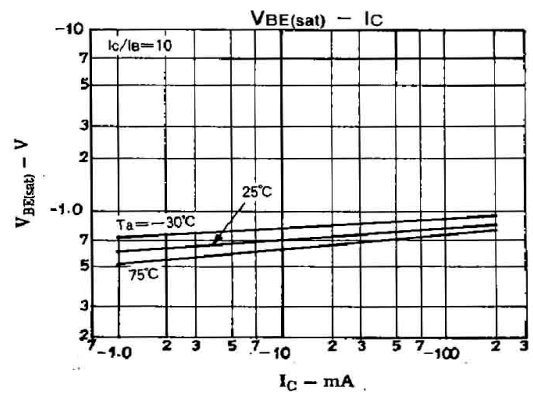
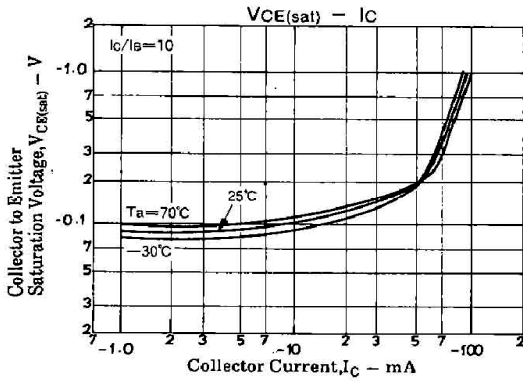
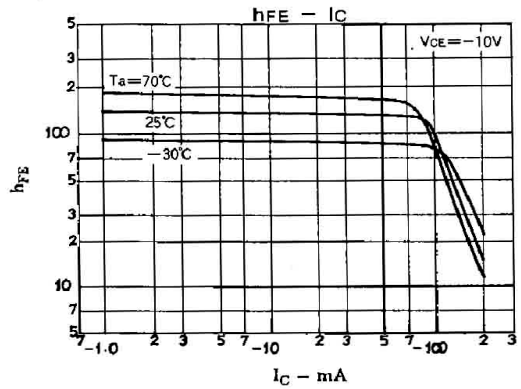
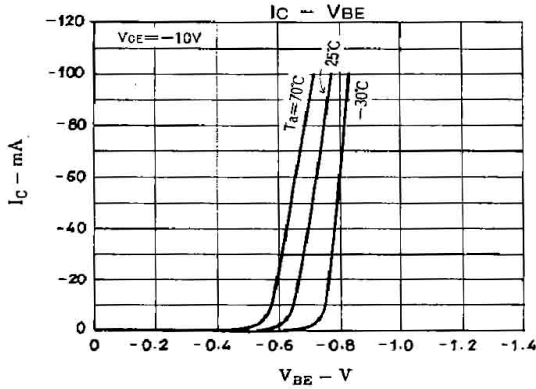
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-400	V
Collector to Emitter Voltage	V_{CEO}	-400	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-200	mA
Collector Current – Continuous(Pulse)	I_{CP}	-400	mA
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ\text{C})$	10	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

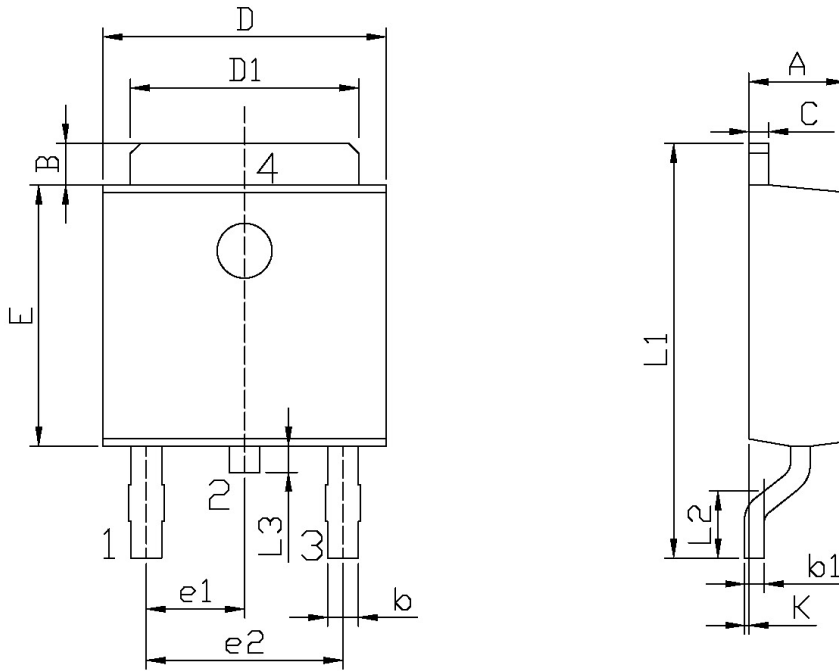
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10\mu\text{A}$ $I_E=0$	-400			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0\text{mA}$ $R_{BE}=\infty$	-400			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu\text{A}$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-300\text{V}$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-4.0\text{V}$ $I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-10\text{V}$ $I_C=-50\text{mA}$	60		200	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-50\text{mA}$ $I_B=-5.0\text{mA}$			-0.8	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-50\text{mA}$ $I_B=-5.0\text{mA}$			-1.0	V
Transition Frequency	f_T	$V_{CE}=-30\text{V}$ $I_C=-10\text{mA}$		70		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-30\text{V}$ $f=1.0\text{MHz}$		5.0		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB}=-30\text{V}$ $f=1.0\text{MHz}$		4.0		pF
Turn-On Time	t_{on}	$10I_{B1}=-10I_{B2}=I_C=50\text{mA}$ $R_L=3\text{K}\Omega$ $R_B=200\Omega$		0.25		μs
Turn-Off Time	t_{off}	at $I_C=50\text{mA}$		5.0		μs

电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

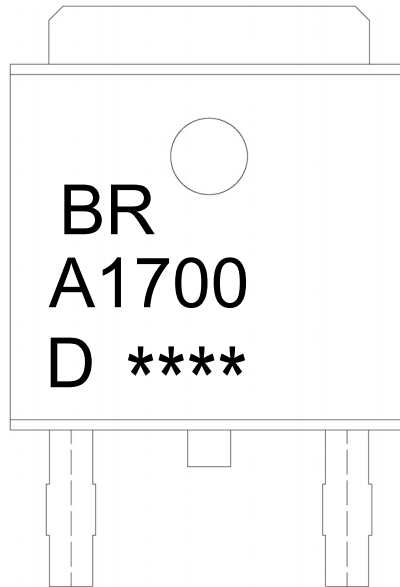


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.70	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252

印章说明 / Marking Instructions



说明：

BR： 为公司代码

A1700： 为型号代码

D： 为 h_{FE} 分档代码

****： 为生产批号代码，随生产批号变化。

Note:

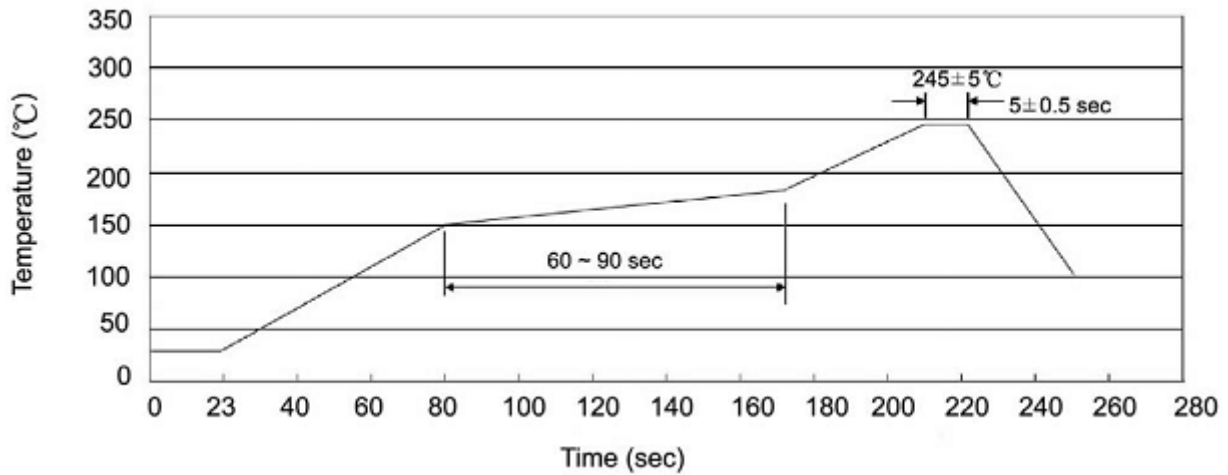
BR: Company Code

A1700: Product Type Code.

D: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	5	25,000	13" × 16	360×360×50	385×257×392

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

使用说明 / Notices